



**Fast Recovery Epitaxial Diode**

**DSEI 30**

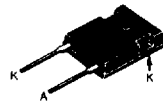
$I_{FAV} = 37\text{ A}$   
 $V_{RRM} = 400\text{-}600\text{ V}$   
 $t_{rr} \leq 35\text{ ns}$

| $V_{RSM}$<br>V | $V_{RRM}$<br>V | Type        |
|----------------|----------------|-------------|
| 440            | 400            | DSEI 30-04A |
| 540            | 500            | DSEI 30-05A |
| 640            | 600            | DSEI 30-06A |



| Symbol     | Test conditions  | Maximum ratings                          |
|------------|--|--|
| $I_{FRMS}$ | 1) $T_{vj} = T_{vjM}$<br>$T_C = 85^\circ\text{C}$ ; rectangular, $\delta = 0.5$<br>$t_r < 10\ \mu\text{s}$ ; rep. rating, pulse width limited by $T_{vjM}$ | 70 A                                     |
| $I_{FAVM}$ |  | 37 A                                     |
| $I_{FRM}$  |  | 375 A                                    |
| $I_{FSM}$  | $T_{vj} = 45^\circ\text{C}$ ; $t = 10\text{ ms}$ (50 Hz), sine<br>$t = 8.3\text{ ms}$ (60 Hz), sine  | 300 A<br>320 A                           |
|            | $T_{vj} = 150^\circ\text{C}$ ; $t = 10\text{ ms}$ (50 Hz), sine<br>$t = 8.3\text{ ms}$ (60 Hz), sine   | 260 A<br>280 A                           |
| $i_{pdt}$  | $T_{vj} = 45^\circ\text{C}$ ; $t = 10\text{ ms}$ (50 Hz), sine<br>$t = 8.3\text{ ms}$ (60 Hz), sine  | 450 A <sup>2</sup><br>420 A <sup>2</sup> |
|            | $T_{vj} = 150^\circ\text{C}$ ; $t = 10\text{ ms}$ (50 Hz), sine<br>$t = 8.3\text{ ms}$ (60 Hz), sine   | 340 A <sup>2</sup><br>320 A <sup>2</sup> |
| $T_{vj}$   |  | -40...+150 °C                            |
| $T_{vjM}$  |  | 150 °C                                   |
| $T_{MS}$   |  | -40...+150 °C                            |
| $P_{Tot}$  | $T_C = 85^\circ\text{C}$   | 65 W                                     |
| $M_s$      | Mounting torque  | 45-55 Ncm                                |
| Weight     |  | 6 g                                      |

TO-247 AD



A = Anode K = Cathode

**Features**

- International standard package
- Glass passivated chips
- Very short recovery time
- Extremely low losses at high switching frequencies
- Low  $I_{FRM}$  values
- Soft recovery behaviour

**Applications**

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

**Advantages**

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses
- Operating at lower temperature or space saving by reduced cooling

| Symbol     | Test conditions   | Characteristics   |
|------------|---|-------------------|
|            |   | typ. max.         |
| $I_R$      | $T_{vj} = 25^\circ\text{C}$ $V_R = V_{RRM}$   | 1.5 mA            |
|            | $T_{vj} = 25^\circ\text{C}$ $V_R = 0.8 \cdot V_{RRM}$   | 250 $\mu\text{A}$ |
|            | $T_{vj} = 125^\circ\text{C}$ $V_R = 0.8 \cdot V_{RRM}$  | 7 mA              |
| $V_F$      | $I_F = 43\text{ A}$ ; $T_{vj} = 150^\circ\text{C}$  | 1.4 V             |
|            | $T_{vj} = 25^\circ\text{C}$   | 1.6 V             |
| $V_{TO}$   | For power-loss calculations only  | 1.01 V            |
| $r_f$      | $T_{vj} = T_{vjM}$  | 7.1 m $\Omega$    |
| $R_{thJC}$ |   | 1 K/W             |
| $R_{thJA}$ |   | 35 K/W            |
| $t_{rr}$   | $I_F = 1\text{ A}$ ; $di/dt = -15\text{ A}/\mu\text{s}$ ; $V_R = 30\text{ V}$ ; $T_{vj} = 25^\circ\text{C}$ | 35 ns             |
| $I_{RM}$   | $V_R = 350\text{ V}$ ; $I_F = 30\text{ A}$ ; $di/dt = -240\text{ A}/\mu\text{s}$                            | 10                |
|            | $L \leq 0.05\ \mu\text{H}$ ; $T_{vj} = 100^\circ\text{C}$   | 15 A              |

1)  $I_{FRM}$  Rating includes reverse blocking losses at  $T_{vjM}$ ,  $V_R = 0.8 V_{RRM}$ , duty cycle  $\delta = 0.5$   
 Standards: DIN/IEC 747

DSEI 30, 400-600 V

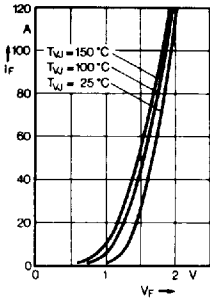


Fig. 1 Forward current versus voltage drop.

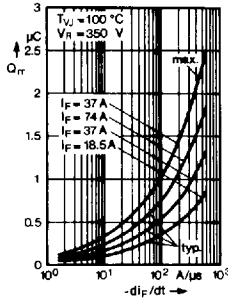


Fig. 2 Recovery charge versus  $-di_F/dt$ .

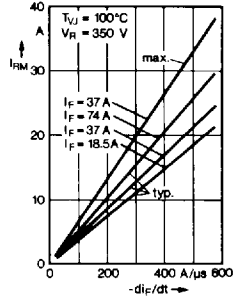


Fig. 3 Peak reverse current versus  $-di_F/dt$ .

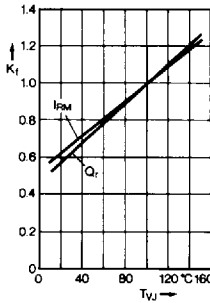


Fig. 4 Dynamic parameters versus junction temperature.

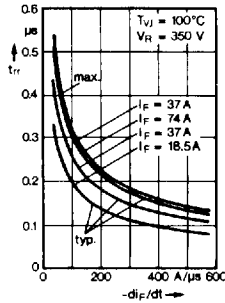


Fig. 5 Recovery time versus  $-di_F/dt$ .

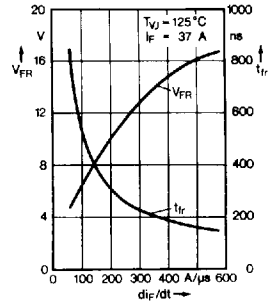


Fig. 6 Peak forward voltage versus  $-di_F/dt$ .

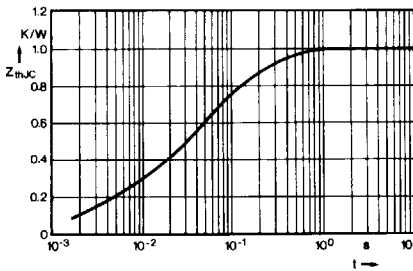
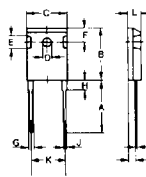


Fig. 7 Transient thermal impedance junction to case.

Dimensions



| Dim. | Millimeter |       | Inches |       |
|------|------------|-------|--------|-------|
|      | Min.       | Max.  | Min.   | Max.  |
| A    | 19.81      | 20.32 | 0.780  | 0.800 |
| B    | 20.80      | 21.46 | 0.819  | 0.845 |
| C    | 15.75      | 16.26 | 0.610  | 0.640 |
| D    | 3.55       | 3.65  | 0.140  | 0.144 |
| E    | 4.32       | 5.48  | 0.170  | 0.216 |
| F    | 5.4        | 8.2   | 0.212  | 0.244 |
| G    | 1.65       | 2.13  | 0.065  | 0.084 |
| H    | -          | 4.5   | -      | 0.177 |
| J    | 1.0        | 1.4   | 0.040  | 0.055 |
| K    | 10.8       | 11.0  | 0.426  | 0.433 |
| L    | 4.7        | 5.3   | 0.185  | 0.209 |
| M    | 0.4        | 0.8   | 0.016  | 0.031 |
| N    | 1.5        | 2.49  | 0.067  | 0.102 |